**1.Material** Substrate GaP (N Type) Epitaxial Layer GaP (P/N Type)

**2.Electrode** N (Cathode) Side Gold Alloy

P (Anode) Side Gold Alloy

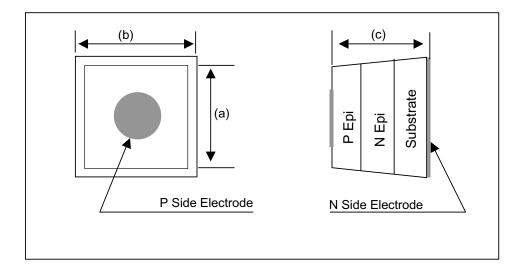
## 3. Electro-Optical Characteristics

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Forward Voltage	V <sub>F(1)</sub>		1.8		V	I <sub>F</sub> =1mA
	V <sub>F(2)</sub>		2.2	2.5	V	I <sub>F</sub> =20mA
Reverse Voltage	$V_R$	6.0			V	I <sub>R</sub> =10μΑ
Brightness	I <sub>V</sub>	20	35		mcd	I <sub>F</sub> =20mA
Wavelength	Hue		700		nm	I <sub>F</sub> =20mA
	Δλ	•	100		nm	I <sub>F</sub> =20mA

\* Note: Assembled into T1<sup>3</sup>/<sub>4</sub> plastic package.

## 4. Mechanical Data

- (a) Emission Area ------ 10mil imes 10mil
- (b) Bottom Area ----- 12mil  $\times$  12mil
- (c) Chip Thickness ----- 11mil



Knowledge\*on Inc.

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